

METHOD AND APPARATUS FOR MANUFACTURING ACTIVE MATRIX DEVICE INCLUDING TOP GATE TYPE TFT

Abstract of Disclosure

A method and an apparatus are provided for manufacturing an active matrix device including a top gate type TFT. A manufacturing process of the top gate type TFT includes the steps of forming an oxide film on the inner wall of a CVD processing chamber and arranging a substrate having source and drain electrodes formed thereon in the processing chamber. Additional steps include doping the source and drain electrodes with P, and forming an a-Si layer and a gate insulating film in the processing chamber. Furthermore, an apparatus is provided for manufacturing an active matrix device including a top gate type TFT having the inner surface of the processing chamber coated with the oxide film.

Figures